

2N7002BK 60 V, 350 mA N-channel Trench MOSFET Rev. 1 – 17 June 2010

Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ESD protection up to 2 kV
- AEC-Q101 qualified

1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1.Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	$T_{amb} = 25 \ ^{\circ}C$	-	-	60	V
V _{GS}	gate-source voltage	T _{amb} = 25 °C	-	-	±20	V
I _D	drain current	$T_{amb} = 25 \text{ °C};$ $V_{GS} = 10 \text{ V}$	<u>[1]</u> -	-	350	mA
R _{DSon}	drain-source on-state resistance	T _j = 25 °C; V _{GS} = 10 V; I _D = 500 mA	-	1	1.6	Ω

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



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2. Pinning information

Table 2.	Pinning			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		2
2	S	source		D
3	D	drain	1 2	
				017aaa000

3. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
2N7002BK	TO-236AB	plastic surface-mounted package; 3 leads	SOT23		

4. Marking

Table 4. Marking codes	
Type number	Marking code ^[1]
2N7002BK	LN*
[1] * = -: made in Hong Kong	

- * = p: made in Hong Kong
- * = t: made in Malaysia
- * = W: made in China

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _{amb} = 25 °C	-	60	V
V_{GS}	gate-source voltage	T _{amb} = 25 °C	-	±20	V
I _D	drain current	V _{GS} = 10 V	<u>[1]</u>		
		T _{amb} = 25 °C	-	350	mA
		T _{amb} = 100 °C	-	245	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \leq$ 10 μs	-	1.2	А

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Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	total power dissipation	on $T_{amb} = 25 \ ^{\circ}C$	[2] -	370	mW
			<u>[1]</u> -	440	mW
		T _{sp} = 25 °C	-	1.2	W
Tj	junction temperature			150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C
Source-d	Irain diode				
I _S	source current	T _{amb} = 25 °C	<u>[1]</u> -	350	mA
ESD max	kimum rating				
V _{ESD}	electrostatic discharge voltage	human body model	<u>[3]</u> _	2000	V

Table 5. Limiting values ... continued

(150 60124)

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

Measured between all pins. [3]

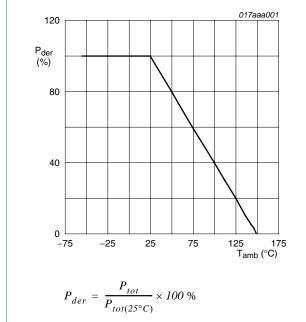
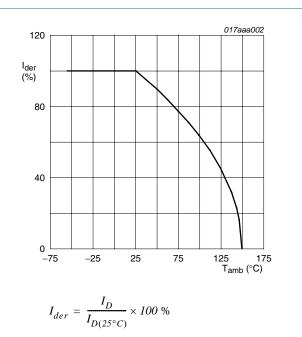


Fig 1. Normalized total power dissipation as a function of ambient temperature



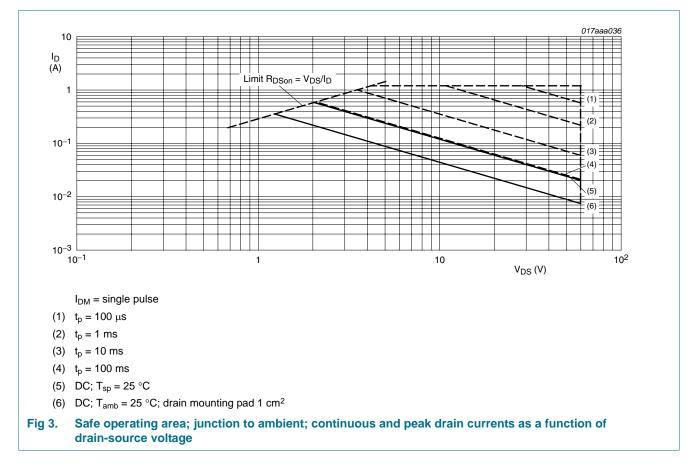


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6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	295	340	K/W
			[2] _	250	285	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	105	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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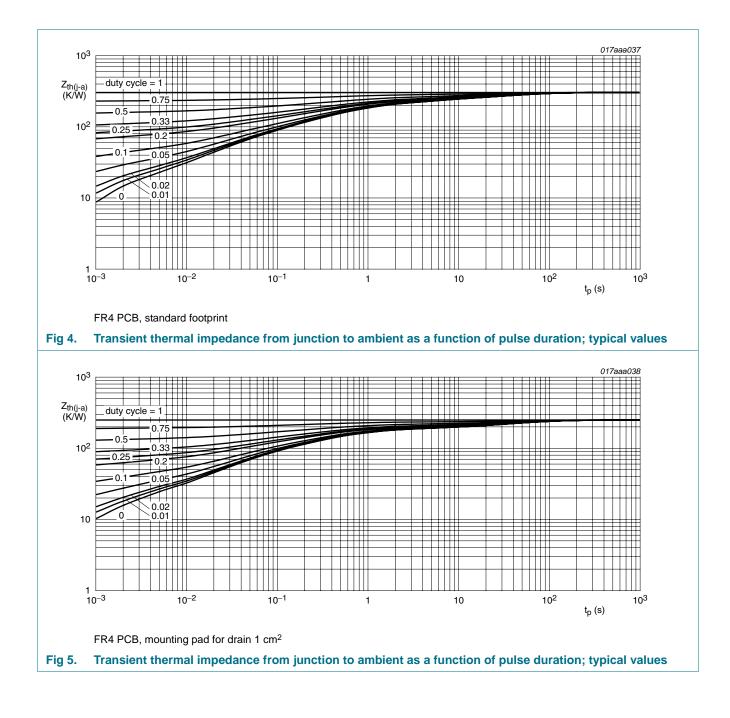
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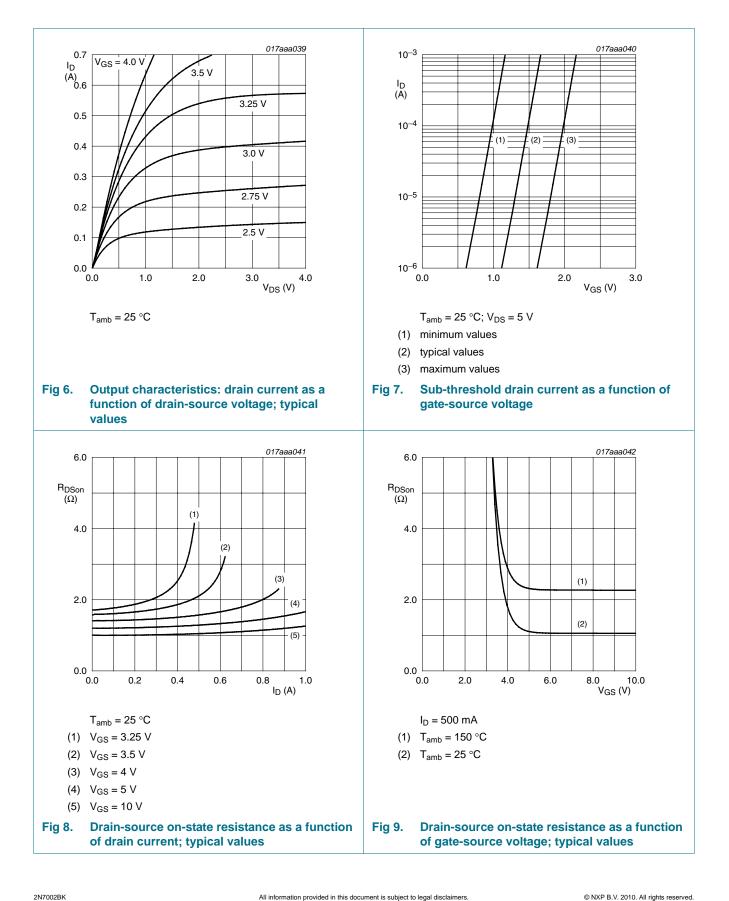
7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 10 \ \mu\text{A}; \ V_{GS} = 0 \ V$	60	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 250 \ \mu\text{A}; \ V_{DS} = V_{GS}$	1.1	1.6	2.1	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}$				
		T _j = 25 °C	-	-	1	μA
		T _j = 150 °C	-	-	10	μA
I _{GSS}	gate leakage current	V_{GS} = ± 20 V; V_{DS} = 0 V	-	-	10	μA
R _{DSon}	drain-source on-state		<u>[1]</u>			
	resistance	V_{GS} = 5 V; I _D = 50 mA	-	1.3	2	Ω
		V_{GS} = 10 V; I_{D} = 500 mA	-	1	1.6	Ω
9fs	forward transconductance	V_{DS} = 10 V; I _D = 200 mA	<u>[1]</u> _	550	-	mS
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	I _D = 300 mA;	-	0.5	0.6	nC
Q _{GS}	gate-source charge	[−] V _{DS} = 30 V; - V _{GS} = 4.5 V	-	0.2	-	nC
Q _{GD}	gate-drain charge	$-v_{GS} = 4.5 v$	-	0.1	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 10 V;$	-	33	50	pF
C _{oss}	output capacitance	f = 1 MHz	-	7	-	pF
C _{rss}	reverse transfer capacitance		-	4	-	pF
t _{d(on)}	turn-on delay time	V _{DD} = 50 V;	-	5	10	ns
t _r	rise time	$R_L = 250 \Omega;$ -V _{GS} = 10 V; $R_G = 6 \Omega$	-	6	-	ns
t _{d(off)}	turn-off delay time		-	12	24	ns
t _f	fall time		-	7	-	ns
Source-dr	ain diode					
V _{SD}	source-drain voltage	I _S = 115 mA; V _{GS} = 0 V	0.47	0.75	1.1	V

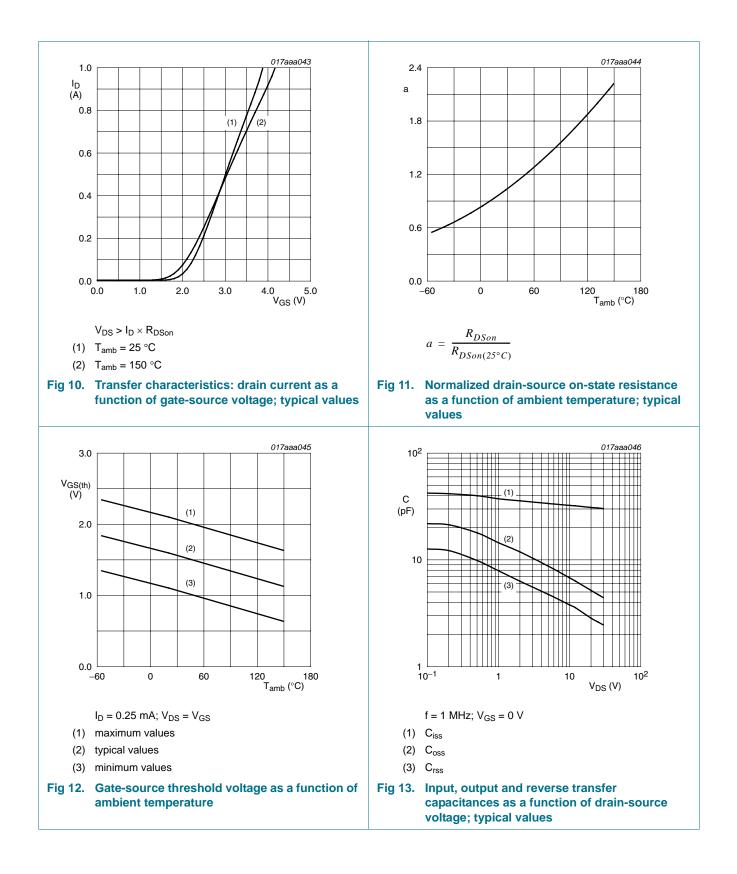
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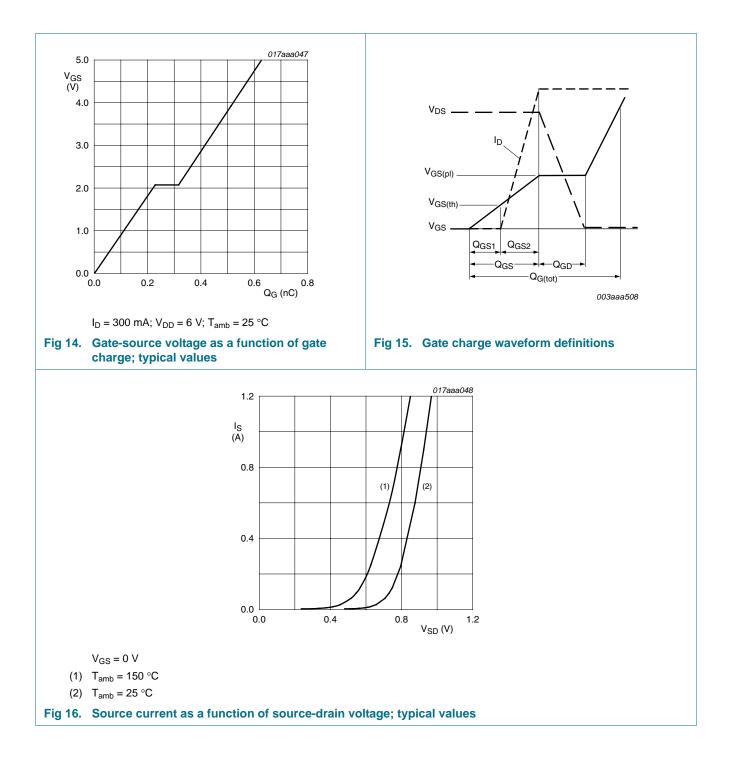
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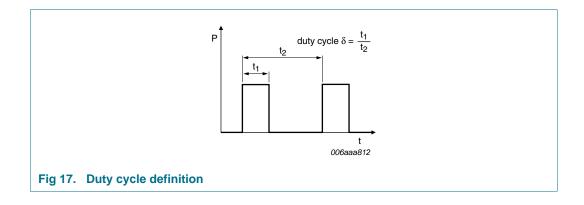
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8. Test information



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9. Package outline

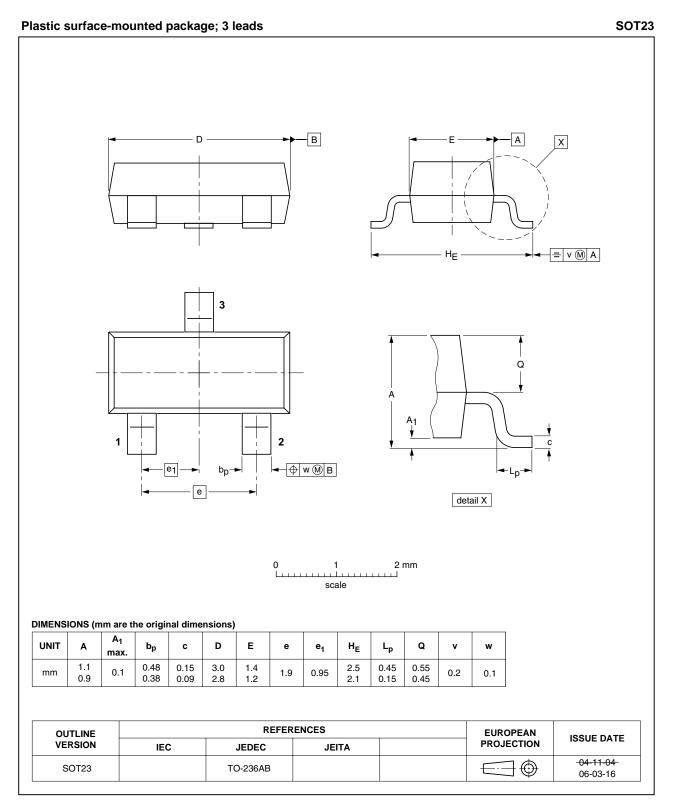
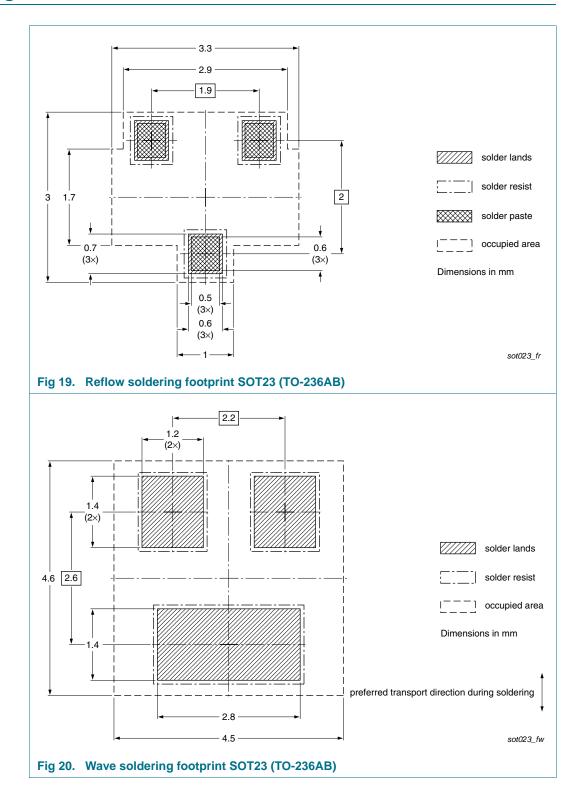


Fig 18. Package outline SOT23 (TO-236AB)

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10. Soldering



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11. Revision history

Table 8. Rev	Revision history					
Document ID	Release date	Data sheet status	Change notice	Supersedes		
2N7002BK v.1	20100617	Product data sheet	-	-		

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12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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